QUESTION #1

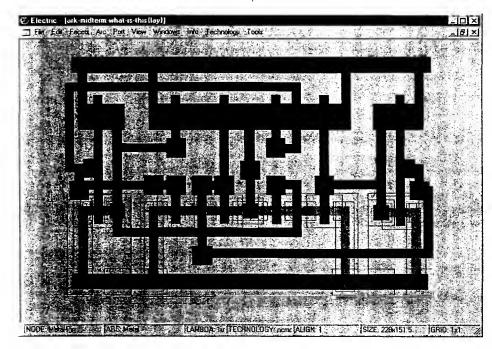
99 miderm

MARKS: 15(5+5+3+2)

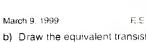
Being able to "reverse engineer" the layout of a facet (cell) is an important skill to verify the functionality of the cell as well as to uncover any layout errors. All the parts of this question relate to me diagram of the facet (cell) on this page.

i) Identify the various layers by running coloured lines through the centre of each polygon (do not bother shading in the whole polygon as that will take too much of your time). Use red for polysilicon, blue for metal1, black for metal2, green for n+ diffusion, yellow/orange for p+ diffusion, brown for p-well, "x" for contact cuts, and "o" for vias. If you need to use additional or different colours, make sure to provide a legend on your diagram.

Question #1 a) Work Sheet



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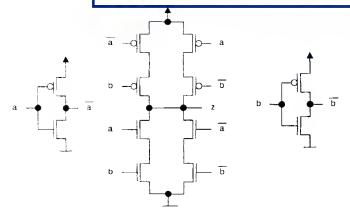
c) What function does this cell

d) What two things are missing

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1b)



1c)

Α		В	1	Z
0		0		0
0		1		1
1		0		1
1	1	1		0

This cell provides an "XOR" function.

- ld) Two things missing
 - Substrate connections to Vdd
 - · Connection to GND for middle p-well.

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QUESTION #2

MARKS: 15 (5 + 5 + 5)

Consider the following three (3) parts of this question. For each of the parts, provide a short explaination. Do all three (3).

a) Describe two common techniques whereby the oxide of sillcon, SiO₂, is grown on crystalline silicon wafers.

Question #2 a) Work Sheet

- Wet oxidation. Heating silicon wafers in an oxidizing atmosphere containing water vapour.
 Temperature usually between 900C and 1000C. This is a rapid process.
- Dry oxidation. The oxidizing atmosphere is pure oxygen. Temperature around 1200C to achieve an acceptable growth rate.

So I jump ship in Hong Kong and make my way over to Tibet, and I get on as a looper at a course over in the Himalayas. A looper, you know, a caddy, a looper, a jock. So, I tell them I'm a pro jock, and who do you think they give me? The Dalai Lama, himself. Twelfth son of the Lama. The flowing robes, the grace, bald... striking. So, I'm on the first tee with him. I give him the driver. He hauls off and whacks one---big hitter, the Lama---long, into a ten thousand foot crevasse, right at the base of this glacier. Do you know what the Lama says? Gunga galunga... gunga, gunga-galunga. So we finish the eighteenth and he's gonna stiff me. And I say, "Hey, Lama, hey, how about a little something, you know, for the effort, you know." And he says, "Oh, uh, there won't be any money, but when you die, on your deathbed, you will receive total consciousness." So I got that goin' for me, which is nice.

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b) Describe the behavior of an n-channel transistor in the various regions (i.e., cut-off, linear or triode, and saturation). Include the appropriate I_{DS} equations and operating conditions for each region.

Question #2 b) Work Sheet

- Cut-off. Occurs when Vgs <= Vt. lds = 0. Translstor is effectively "off".
- Linear. Occurs when 0 < Vds < (Vgs Vt).

$$I_{DS} = \beta \left[\left(V_{GS} - V_T \right) V_{DS} - \frac{{V_{DS}}^2}{2} \right]$$

lds varies roughly linearly with Vds for a particular Vgs (assuming Vds << (Vgs-Vt)),

Transistor acts almost like a resistor.

Saturation. Occurs when 0 < (Vgs - Vt) < Vds.

$$I_{DS} = \beta \left[\frac{\left(V_{GS} - V_T \right)^2}{2} \right]$$

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Ids is a constant depending on Vgs. Transistor acts like a constant current source.

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c) For an n-channel transistor, plot the drain-source current as a function of the drain-source voltage for various selections of the gate-source voltage. Where necessary, use device parameters as indicated on Page 2 of the examination paper.

Question #2 c) Work Sheet

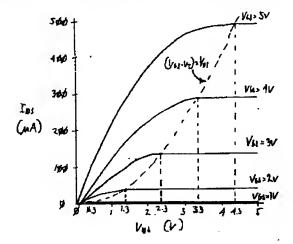
At saturation,

$$I_{DS} = \beta \left[\frac{(V_{GS} - V_r)^2}{2} \right]$$

$$\beta = \frac{\mu \varepsilon}{t_{ox}} \frac{W}{L} = \frac{775x3.9x8.85x10^{-14}}{5x10^{-6}} \frac{3um}{3um} = 5.35x10^{-5}$$

Vgs	Ids (Saturation) (uA)
1	2.4
2	45
3	142
4	291
5	495

Knee between saturation and linear occurs at (Vgs - Vt) = Vds



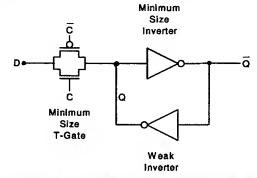
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QUESTION #3 MARKS: 15 (7 + 8)

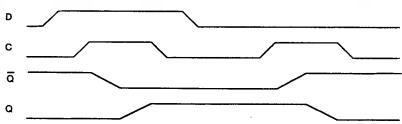
Consider the following circuit. It is a variation of the T-Latch that you analyzed as part of one of your assignments. Note that the T-Gate in the feedback loop is missing and that the inverter in the feedback loop is NOT a Minimum Size Inverter. Instead it has been replaced with a Weak Inverter (also known as a Trickle Inverter).

Note that a CMOS3DLM Minimum Size Inverter has a n-channel pull-down transistor of size 3μm:3μm (W:L) and a p-channel pull-up transistor of size 9μm:3μm (W:L). As well a CMOS3DLM Minimum Size T-Gate has a n-channel transistor of size 3μm:3μm (W:L) in parallel with a p-channel transistor of size 9μm:3μm (W:L).

In order for this circuit to work property, the bottom inverter must be a Weak Inverter. A Weak Inverter is one with a low β . The β must be chosen so that the circuit driving the D input can "override" the output of the Weak Inverter if the two output signals (the output of the circuit driving the D input and the output of the Weak Inverter driving the Q node) are in the opposite state. This would occur if the T-Latch was loading a D input that was a complementary value of the Q node (i.e., D=0 when Q=1 or D=1 when Q=0).



See the waveforms below for an Illustrative (not to scale) example of the operation of the circuit.



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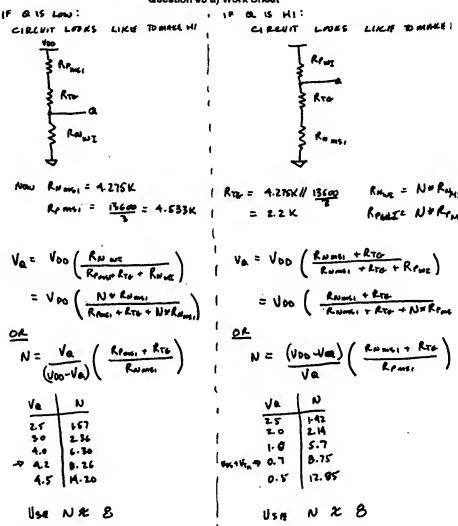
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a) Assuming the device driving the D Input is a Minimum Size Inverter, calculate the β of the Weak Inverter needed for the circuit to operate correctly. Hint: When the T-Latch is changing state, the circuit can effectively be modelled as a resistive voltage divider.

Question #3 a) Work Sheet



b) As well as determining the β of the Weak inverter, the clock signal, C, must satisfy certain criteria. In particular the length of time the C input is asserted (i.e., logical 1) must be long enough for the output and Q node to stabilize. Calculate the minimum length of time the C input must be asserted for the circuit of Part 3 a) to work property.

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Assume the following (you may also make other appropriate assumptions):

- Assume Ons propagation delay from the C input to the input/output of the T-Gate.
- · Assume 2ns rise and fall times of the C input.
- Assume the D input has stabilized before the C input is asserted.
- Assume that the only load capacitances are the gate capacitances of the transistors.
- Assume 10%-90% (90%-10%) rise (fall) times are the same as the 0%-100% (100%-0%) rise (fall) times.

Question #3 b) Work Sheet

By VOD By VOO E BY VOD BY VOD BY VOD

= 3×3×6.9 ×0-4 pf/m2 = 3×3×6.9 ×0-4 pf/m2

Bp = 3 x 17.2 x40 -6 My = 51.6 x10 -6 A/42 Bn = 53.5 x10 -6 A/A

ASSUME NO RESISTIVE BEFECT THROW THATE.

ASSUME Q IS LOW

ASSUME Q IS H

ED = 200 + tra + tra + tra + 200 = los + 3024.86f + 20 M8.4ff + los = los + 3026.600 + 2036.600 + 103 = los + 3024.86f + 20 M8.4ff + los = los + 3026.600 + 2036.600 + 2036.600 + 103

=(1 + .192 + 168 + 1) ns= 3.67 ns = 3.72 ns.

I AM ASSUMED THAT I DON'T HAVE TO WAST WHILE THE WEAR INVENTER COMPLETES ITS TRANSITION SINCE & WOOR IS ALREMOY DRIVEN TO CORNECT STATE.

I AM ALSO ASSUMENCE THAT THE C INFOT CAN BE REMONITING LATER.

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"WHAT ARE YOU LOOKING AT? HAVEN'T YOU EVER SEEN A MAN 50 BROKEN THAT HE JUST HAD TO SPIN?"

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